

60V P-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	12m Ω @-10V	-65A

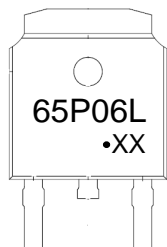
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(on)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

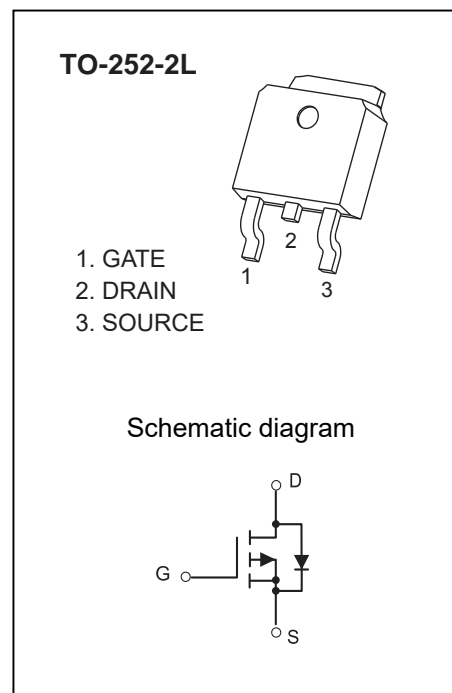
Application

- Power Switching Application

MARKING:



65P06L = Device Code
 XX = Date Code
 Solid Dot = Green Indicator



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	-60	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	-65 A
	$T_C = 100^\circ\text{C}$	I_D	-46 A
Pulsed Drain Current ²	I_{DM}	-260	A
Single Pulsed Avalanche Current ³	I_{AS}	-50	A
Single Pulsed Avalanche Energy ³	E_{AS}	625	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	92 W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.36	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

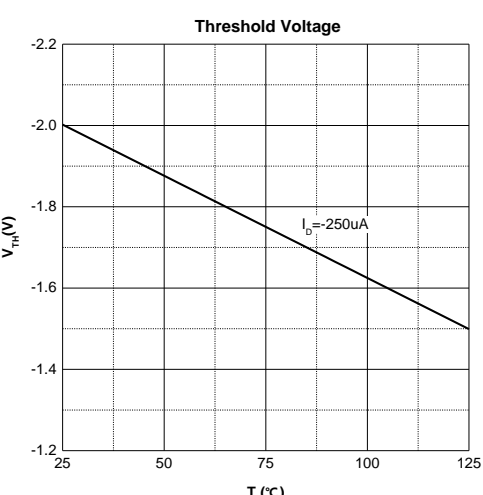
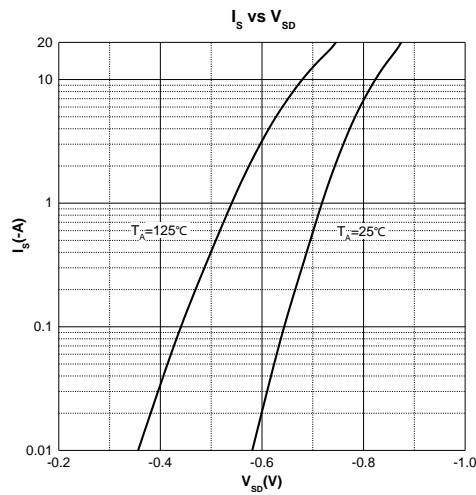
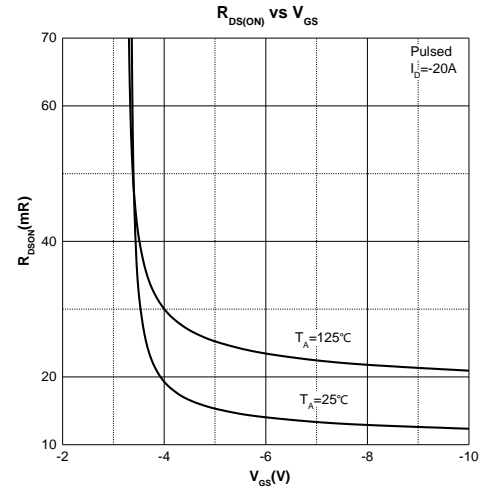
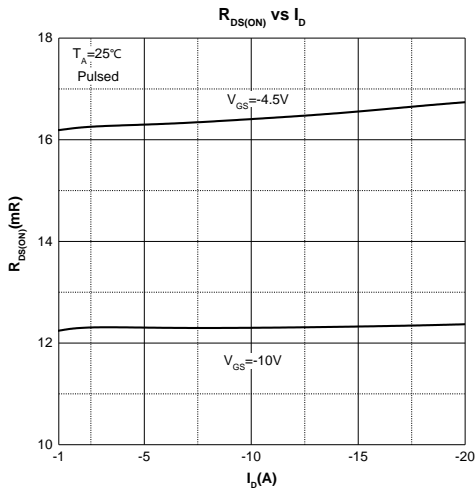
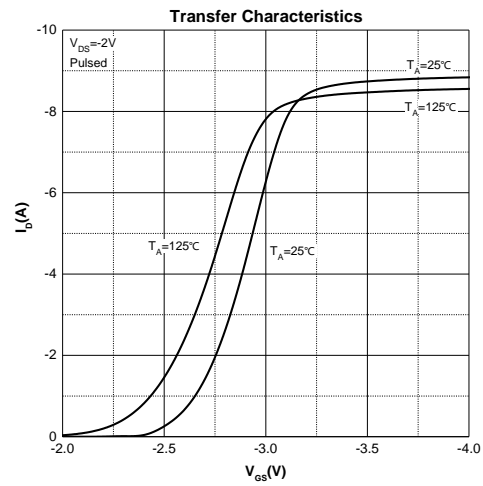
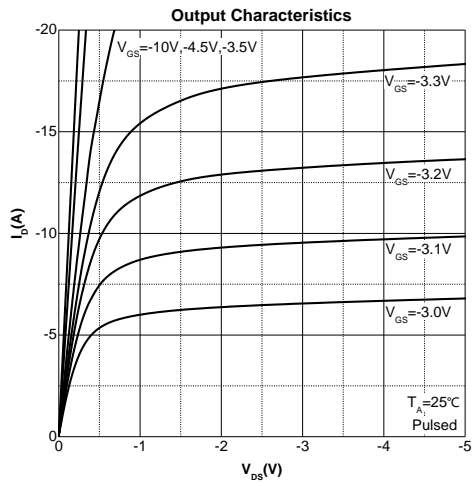
Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-2	-3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -20A$		12	18	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -20A$		25		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -30V, V_{GS} = 0V, f = 1MHz$		6203		pF
Output Capacitance	C_{oss}			346		
Reverse Transfer Capacitance	C_{rss}			299		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.1		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -30V, V_{GS} = -10V, I_D = -20A$		119		nC
Gate-source Charge	Q_{gs}			18		
Gate-drain Charge	Q_{gd}			27		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -30V, V_{GS} = -10V,$ $R_L = 1.5\Omega, R_G = 3\Omega$		11		ns
Turn-on Rise Time	t_r			14		
Turn-off Delay Time	$t_{d(off)}$			36		
Turn-off Fall Time	t_f			15		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = -20A$			-1.2	V

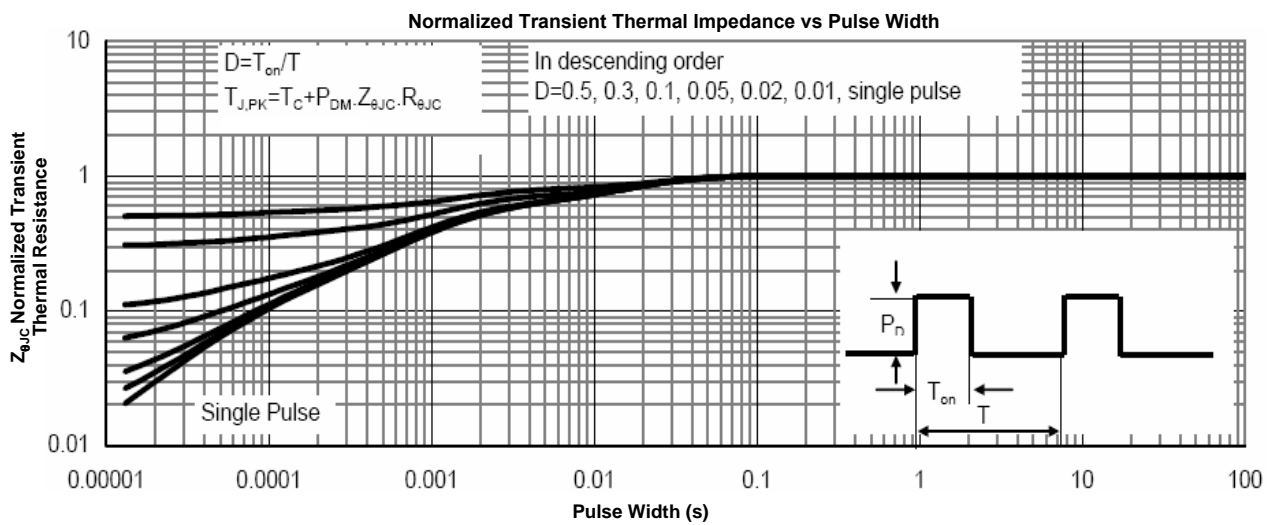
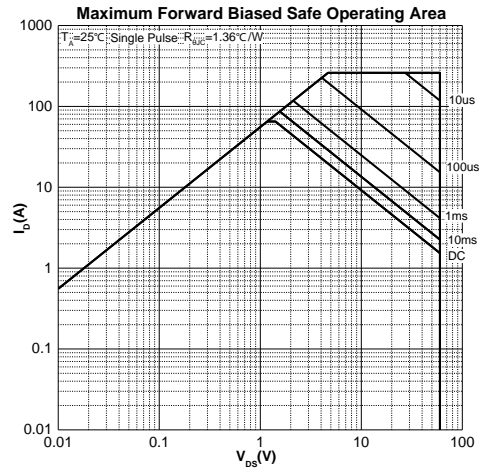
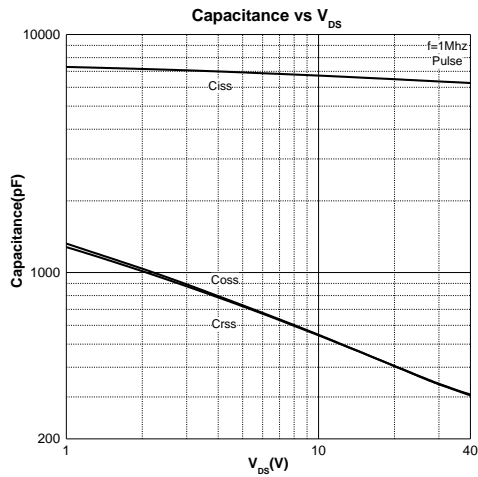
Notes :

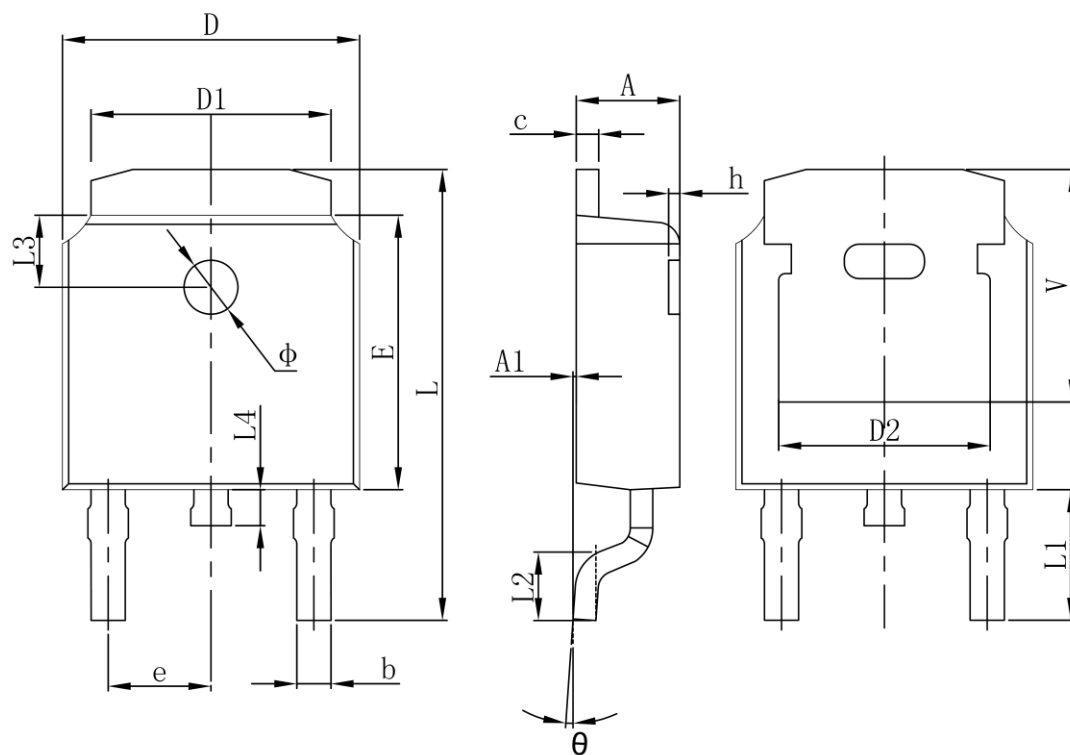
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = -30V, V_{GS} = -10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



Typical Characteristics





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830REF		0.190REF	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900REF		0.114REF	
L2	1.400	1.700	0.055	0.067
L3	1.600REF		0.063REF	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250REF		0.207REF	